

General Description

TRinno IGBT power module provides low conduction and switching losses as well as short circuit ruggedness. It is designed for applications such as Motor Driver, IH , Rectifier and Welder.

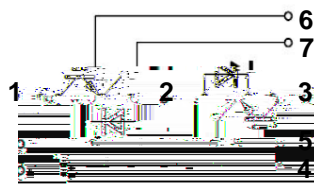
Features

- 1200V NPT Trench IGBT Technology
- Fast & Soft Recovery Diodes
- Positive Temperature Coefficient
- Short Circuit Withstanding Time : 10 s



Applications

Motor driver, IH(Induction heating), Rectifier, Welder



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage	V_{CES}	1200	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	
Continuous Collector Current	I_C	$T_C = 25$	150	A
		$T_C = 100$	75	A
Pulsed Collector Current (Note 1)	I_{CM}	150	A	
Diode Continuous Forward Current	I_F	75	A	
Power Dissipation	P_D	$T_C = 25$	417	W
		$T_C = 100$	166	W
Operating Junction Temperature	T_{vj}	-40 ~ 150		
Storage Temperature Range	T_{STG}	-40 ~ 150		

Notes :

(1) Repetitive rating : Pulse width limited by maximum junction temperature

Thermal Characteristics

Parameter	Symbol	Value	Unit
Typical Thermal resistance, Junction-to-Case (Per ½ Module)		0.3	K/W
Typical Thermal resistance, Junction-to-Case (Per ½ Module)		1.0	K/W

TPM75GB120RHN

2-PACK IGBT Module

Electrical Characteristics of the IGBT $T_{vj}=25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
OFF						
Collector Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0V, I_C = 1mA$	1200	--	--	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0V$	--	--	1	mA
Gate Emitter Leakage Current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	--	--	100	nA
ON						
Gate Emitter Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 250 A$	4.0	--	7.5	V
		$V_{GE} = V_{CE}, I_C = 75mA$	5.0	--	8.5	V
Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	$V_{GE} = 15V, I_C = 75A, T_{vj} = 25$	--	2.3	2.8	V
		$V_{GE} = 15V, I_C = 75A, T_{vj} = 125$	--	2.5	3.0	V
DYNAMIC						
Input Capacitance	C_{IES}	$V_{CE} = 25V,$ $V_{GE} = 0V$ $f = 1MHz$	--	9.5	--	nF
Output Capacitance	C_{OES}		--	530	--	pF
Reverse Transfer Capacitance	C_{RES}		--	70	--	pF
SWITCHING						
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 75A$ $R_G = 2.2 \Omega, V_{GE} = 15V$ Inductive Load, $T_{vj} = 25$	--	48	--	ns
Rise Time	t_r		--	69	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	163	--	ns
Fall Time	t_f		--	47	--	ns
Turn-On Switching Loss	E_{ON}		--	5.7	--	mJ
Turn-Off Switching Loss	E_{OFF}		--	2.4	--	mJ
Total Switching Loss	E_{TS}	--	8.1	--	mJ	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 600V, I_C = 75A$ $R_G = 2.2 \Omega, V_{GE} = 15V$ Inductive Load, $T_{vj} = 125$	--	53	--	ns
Rise Time	t_r		--	74	--	ns
Turn-Off Delay Time	$t_{d(off)}$		--	165	--	ns
Fall Time	t_f		--	56	--	ns
Turn-On Switching Loss	E_{ON}		--	8.2	--	mJ
Turn-Off Switching Loss	E_{OFF}		--	4.1	--	mJ
Total Switching Loss	E_{TS}	--	12.3	--	mJ	
Total Gate Charge	Q_g	$V_{CC} = 600V, I_C = 75A$ $V_{GE} = 15V$	--	635	--	nC
Gate-Emitter Charge	Q_{ge}		--	110	--	nC
Gate-Collector Charge	Q_{gc}		--	285	--	nC
Short Circuit Withstanding Time	t_{sc}	$V_{CC} = 600V, V_{GE} = 15V, T_{vj} = 125$	10	--	--	s

Electrical Characteristics of the DIODE $T_{vj}=25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit	
Diode Forward Voltage	V_{FM}	$I_F = 75\text{A}$	$T_{vj} = 25$	--	1.7	2.5	V
			$T_{vj} = 125$	--	1.8	2.6	
Reverse Recovery Current	I_{rr}	$V_{CC} = 600\text{V}, I_F = 75\text{A}$ $R_G = 2.2, V_{GE} = 15\text{V}$ Inductive Load	$T_{vj} = 25$	--	55	--	A
			$T_{vj} = 125$	--	70	--	
Reverse Recovery Charge	Q_{rr}	$V_{CC} = 600\text{V}, I_F = 75\text{A}$ $R_G = 2.2, V_{GE} = 15\text{V}$ Inductive Load	$T_{vj} = 25$	--	6.5	--	C
			$T_{vj} = 125$	--	12.0	--	
Reverse Recovery Time	t_{rr}	$V_{CC} = 600\text{V}, I_F = 75\text{A}$ $R_G = 2.2, V_{GE} = 15\text{V}$ Inductive Load	$T_{vj} = 25$	--	110	--	ns
			$T_{vj} = 125$	--	120	--	

Characteristics of the Module

Parameter	Symbol	Test condition	Min.	Typ.	Max.	Unit
Isolation Voltage	V_{ISO}	RMS, $f=50\text{Hz}$, $t=1$ minutes	--	2.5	--	kV
Terminal mounting torque (M5)	--		--	3.0	--	N.m
Weight	--		--	170	--	g

IGBT Characteristics

Fig. 1 Output characteristics

Fig. 1

Fig. 2 Saturation voltage characteristics

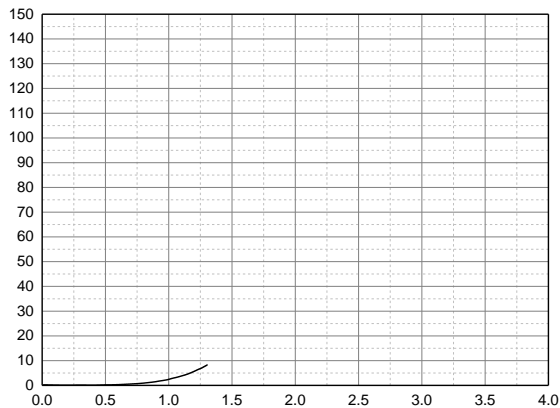


Fig. 3 Turn-on time vs. gate resistor

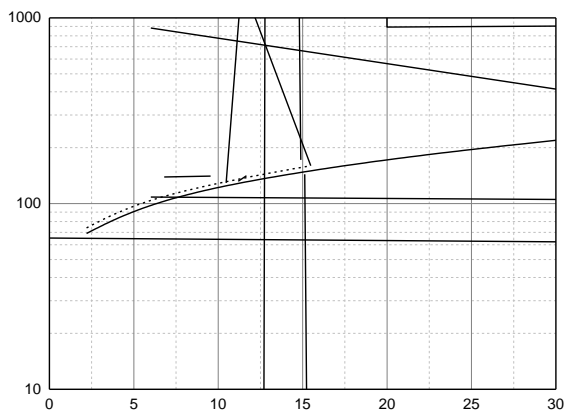


Fig. 4 Turn-off time vs. gate resistor

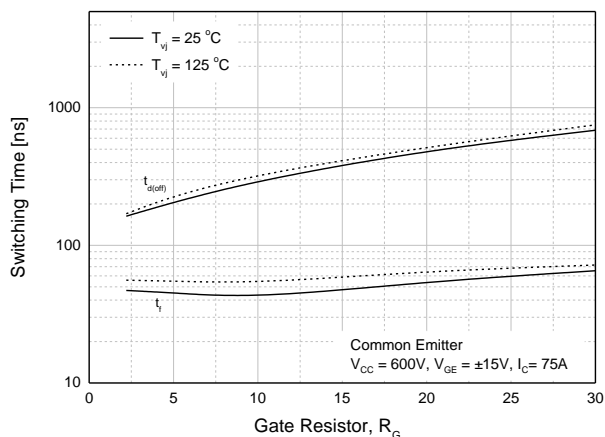


Fig. 5 Switching loss vs. gate resistor

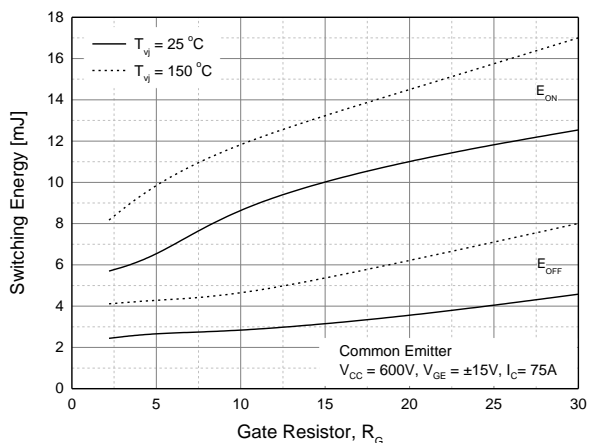
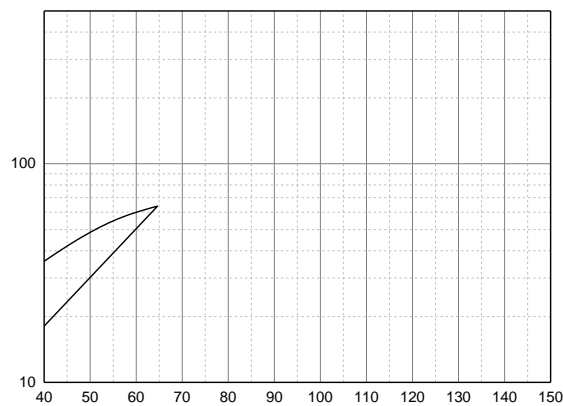


Fig. 6 Turn-on time vs. collector current



IGBT Characteristics

Fig. 7 Turn-off time vs. collector current

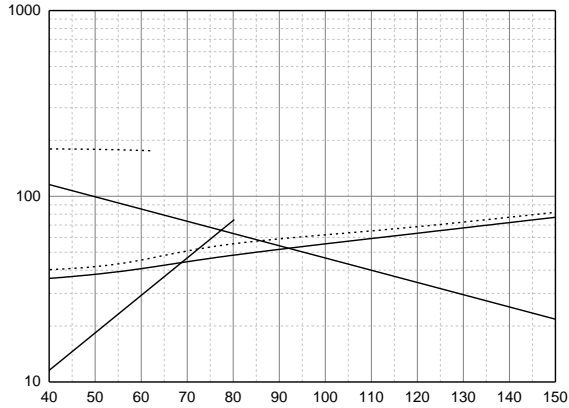


Fig. 8 Switching loss vs. collector current

Fig. 9 Gate charge characteristics

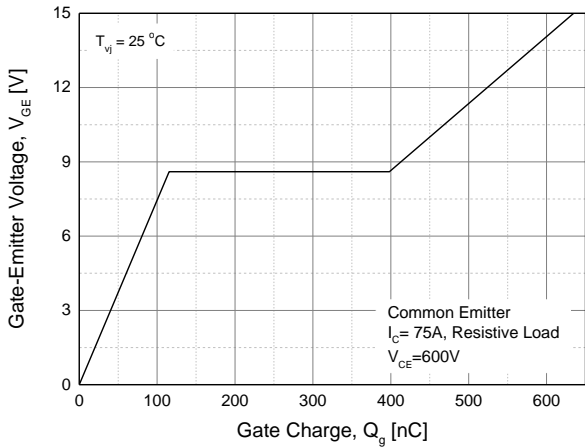


Fig. 10 Transient thermal impedance of IGBT

Fig. 11 SOA

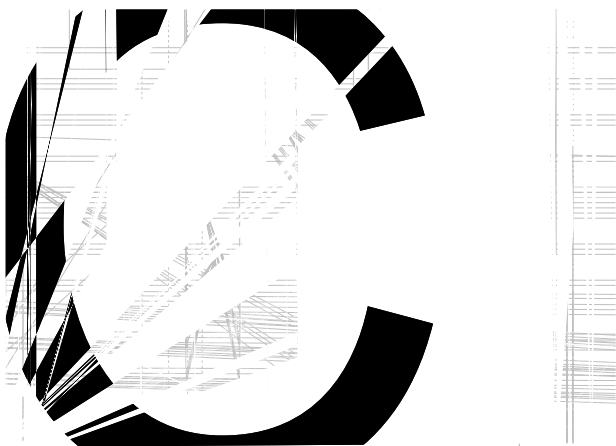
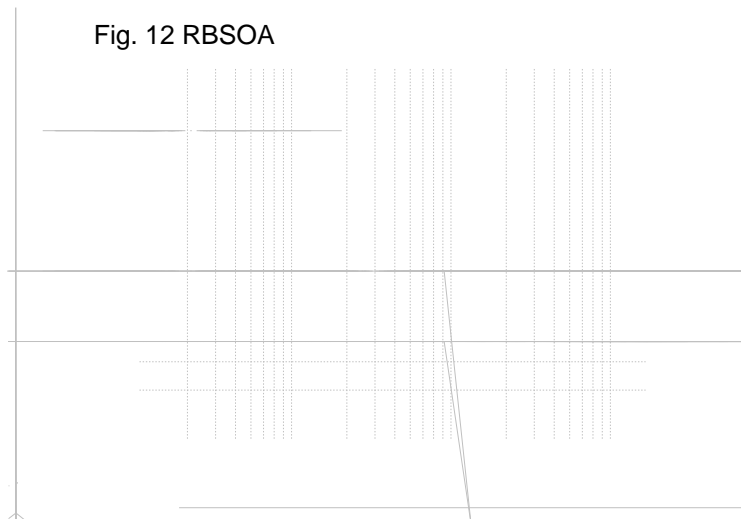
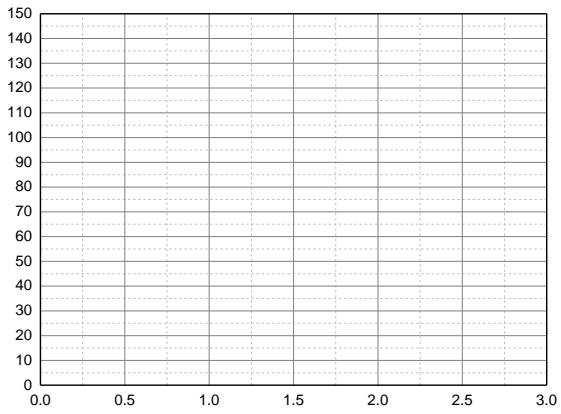


Fig. 12 RBSOA

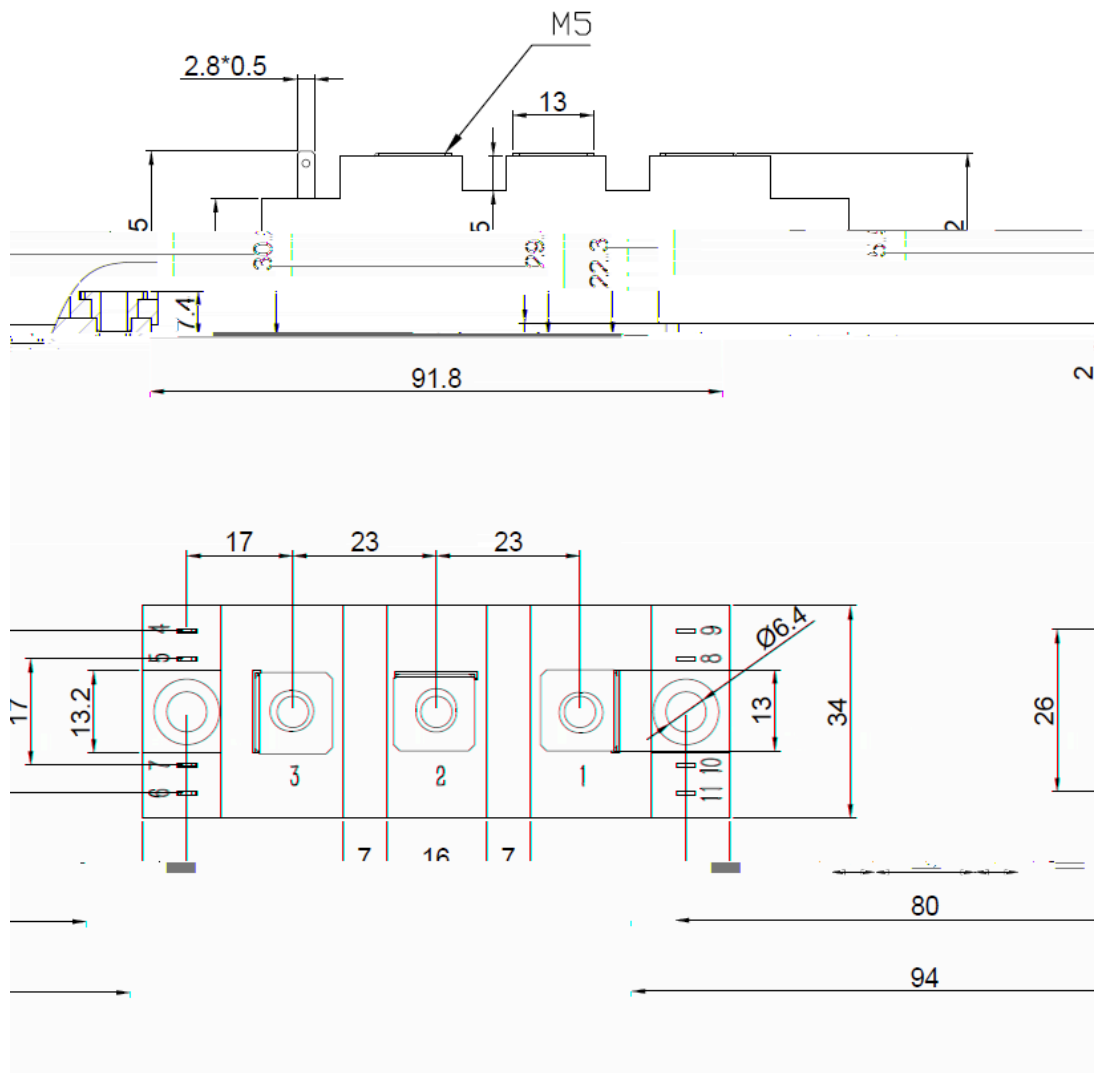


Diode Characteristics

Fig. 13 Conduction characteristics of Diode



Package Outline (Dimension in mm)



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